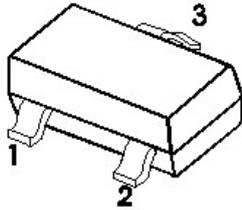


S8050

SOT-23 Plastic-Encapsulate Transistors

SOT-23



1. BASE

2. EMITTER

3. COLLECTOR

Features

- ◆ Complementary to S8550
- ◆ Power Dissipation of 300mW
- ◆ High Stability and High Reliability

Mechanical Data

SOT-23 Small Outline Plastic Package

Epoxy UL: 94V-0

Mounting Position: Any

Marking: J3Y

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current-Continuous	I_C	500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-+150	°C
Thermal resistance From junction to ambient	$R_{\theta JA}$	417	°C/W

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

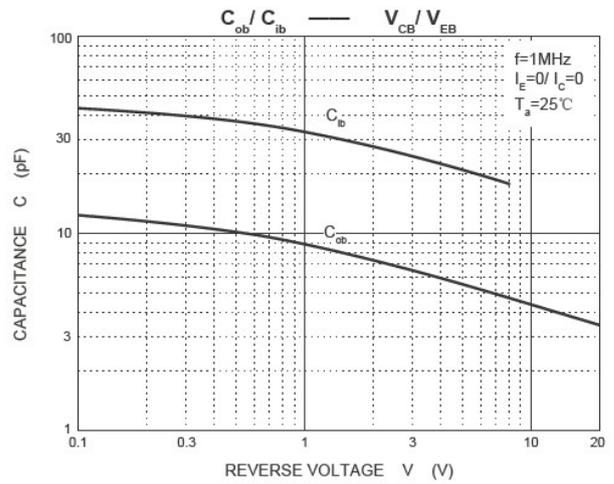
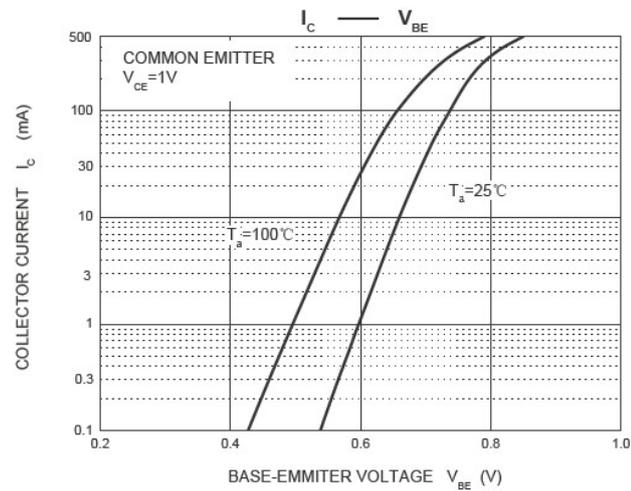
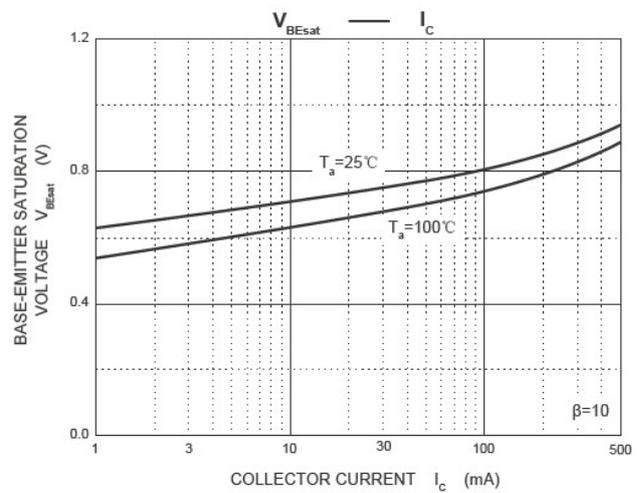
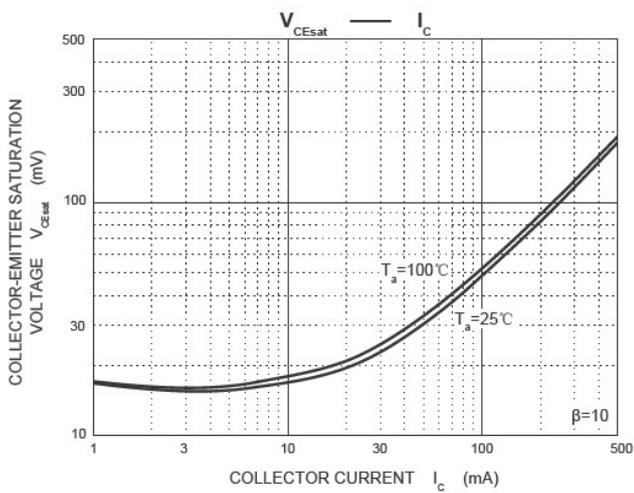
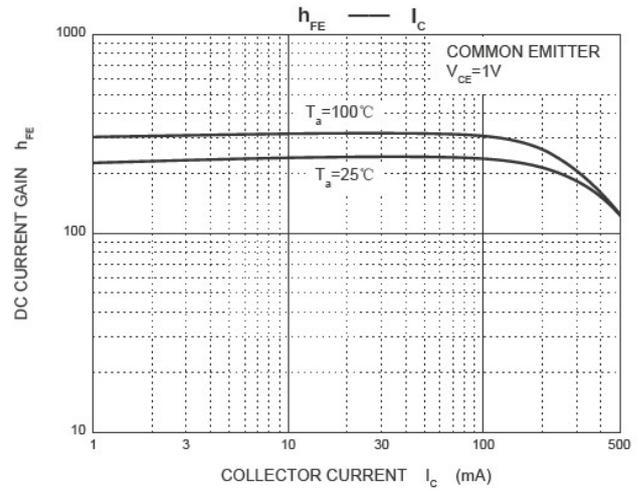
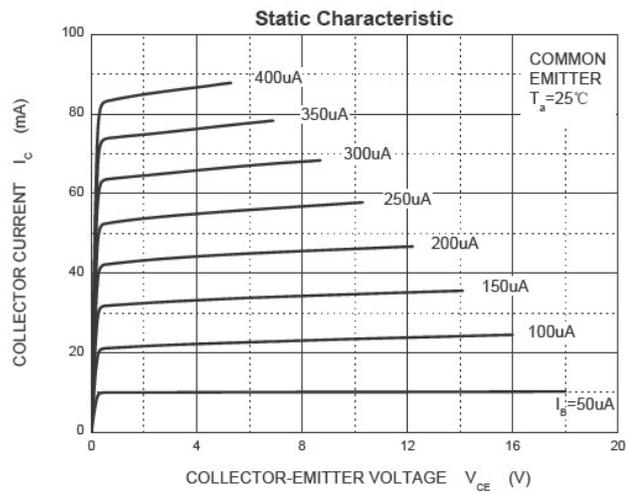
Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5		V
Collector cut-off current	I_{CEO}	$V_{CE}=20V, I_B=0$		100	nA
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$		100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=50mA$	120	400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=500mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.60	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$		1.20	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA, f=30MHz$	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

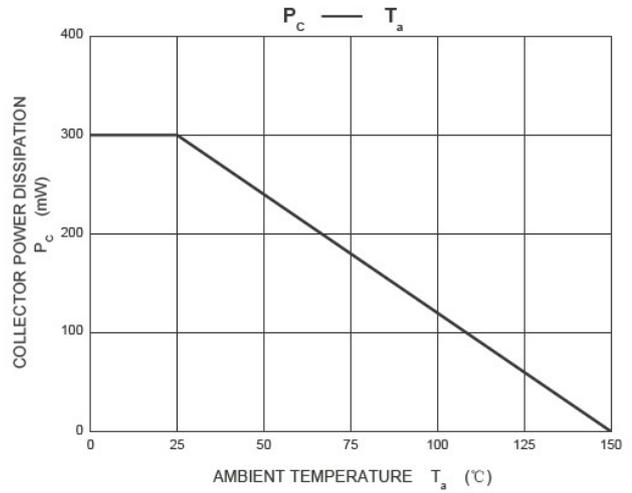
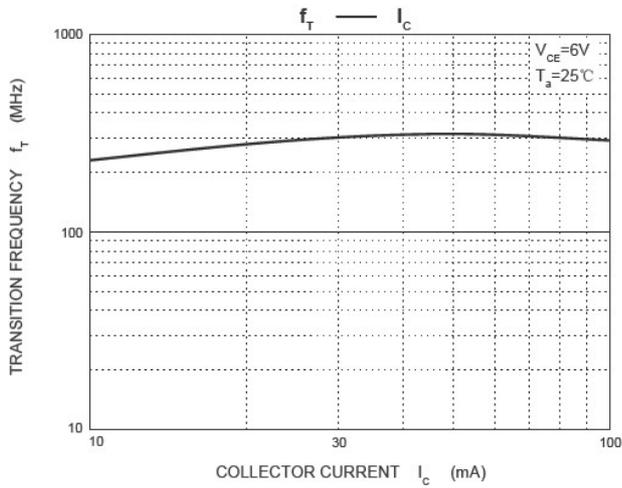
RANK	L	H	J
RANGE	120-200	200-350	300-400

RATINGS AND CHARACTERISTIC CURVES S8050

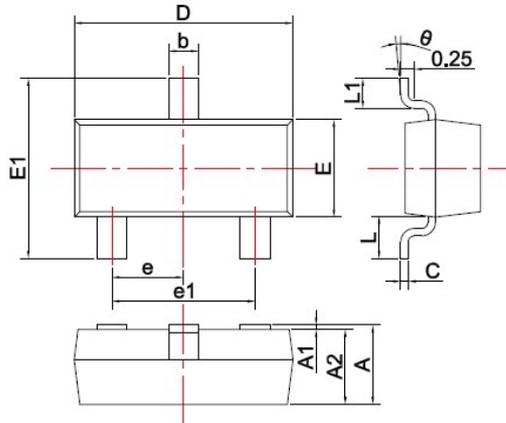
Typical Characteristics



RATINGS AND CHARACTERISTIC CURVES S8050



SOT-23 PACKAGE OUTLINE Plastic surface mounted package

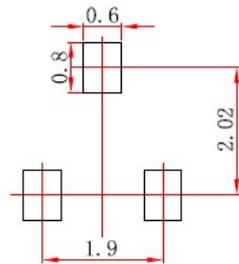


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0 $^\circ$	8 $^\circ$

Unit: mm

Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note:

1. Controlling dimension; in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

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